

## **GUNN Diodes**

Anode Heat Sink

#### MG1041 – MG1059

#### **Features**

- · High Reliability
- · Low-Phase Noise
- 9.5–35.5 GHz Operation
- Pulsed and CW Designs to 20 mW

### **Applications**

- Motion Detectors
- · Transmitters and Receivers
- Beacons
- Automotive Collision Avoidance Radars
- Radars
- Radiometers
- Instrumentation



### Description

Microsemi's GaAs Gunn diodes, epi-up (anode heatsink), are fabricated from epitaxial layers grown at MSC by the Vapor Phase Epitaxy technique. The layers are processed using proprietary techniques resulting in ultra- low phase and 1/f noise. The diodes are available in a variety of microwave ceramic packages for operation from 9.5–35.5 GHz.



### **GUNN Diodes**

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(Discrete Frequency: Anode Heatsink)

CW Epi-Up Gunn Diodes (Specifications @ 25°C)

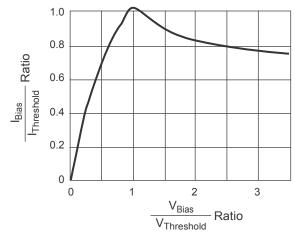
Part Number	Operating Frequency <sup>1</sup> (GHz)	Min. Power² (mW)	Typ. Operating Voltage (V)	Max. Operating Current (mA)	Package Outline³
MG1052-11	9.5–11.5	10	8	140	M11
MG1056-11	9.5–11.5	20	8	200	M11
MG1054-11	23.0–25.0	5	5	200	M11
MG1058-11	23.0–25.0	10	5	300	M11
MG1059-11	33.5–35.5	5	5	300	M11

Pulsed Epi-Up Gunn Diodes (Specifications @ 25°C)

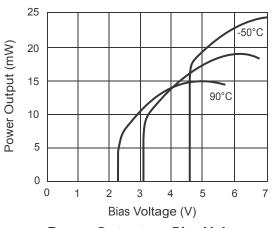
Part Number	Operating Frequency <sup>1</sup> (GHz)	Min. Power² (mW)	Typ. Operating Voltage (V)	Max. Operating Current (mA)	Package Outline³
MG1041-11	9.5–11.5	10	9	110	M11
MG1042-11	9.5–11.5	20	9	140	M11
MG1043-11	9.5–11.5	30	10	180	M11
MG1044-11	23.0–25.0	5	8	120	M11
MG1045-11	23.0–25.0	10	8	150	M11
MG1046-11	23.0–25.0	20	8	200	M11

<sup>&</sup>lt;sup>1</sup>Microsemi Gunn diodes are specified to operate within a narrow range of a customer-designated center frequency within the operating frequency range shown. Additional frequencies are available; Please contact the factory.

# Typical Characteristics



I<sub>Bias</sub> Ratio vs. V<sub>Bias</sub> Ratio



Power Output vs. Bias Voltage

**IMPORTANT:** For the most current data, consult our website: <u>www.MICROSEMI.com</u> Specifications are subject to change. Consult factory for the latest information.

These devices are

These devices are ESD sensitive and must be handled using ESD precautions.

These products are supplied with a RoHS complaint Gold finish.

<sup>&</sup>lt;sup>2</sup>Power is measured using a critically coupled test cavity. For pulsed diodes, pulse width = 1 µS, duty factor = 1% typ.

<sup>&</sup>lt;sup>3</sup> Polarity: cathode is the cap and anode is the heatsink.